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AMENDMENTS TO THE CLAIMS

(The following includes a complete listing of all claims with their current status indicated. Additional language is underscored; deletions are stricken through.)

21. (Currently Amended) A process for making a semiconductor device comprising the steps of:

providing a substrate having at least one semiconductor layer;
forming an underlayer having an opening over the at least one semiconductor layer;

J1 forming a layer of conductive material over the underlayer and in said opening, said layer of conductive material having a topography that includes a substantially vertical component in said opening;

forming an overlayer over the said layer of conductive material;
etching a contact hole in said overlayer and in an overetch amount of the substantially vertical component of said layer of conductive material in said opening; and
forming a contact in said contact hole disposed adjacent to and directly contacting said vertical component.

31. (Currently Amended) A process for making a semiconductor device comprising:

J2 providing a substrate having at least one semiconductor layer;
forming a structure having an opening in said at least one semiconductor layer;
forming a layer of conductive material over said at least one semiconductor layer;
filling said opening with said conductive material to form a substantially vertical component in said opening;

forming an overlayer over said layer of conductive material;
forming a contact hole in said overlayer and is extending into said vertical component of said layer of conductive material, said contact hole disposed adjacent to and directly contacting said vertical component in said opening; and
filling said contact hole with a conducting material.